

# Inverting amplifier and CMOS inverter

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## Abstract

The phase180inverse circuit in eSIM was built to amplify and invert sine wave and then use mirror inversion for noise cancellation application in future. In the common source MOS amplifier circuit both current and voltage gain can be described as medium, but the output is the inverse of the input, i.e. 180deg phase change. A single stage inverting MOSFET amplifier was successfully built using n-MOSFET in enhancement mode. The output of the amplifier drove CMOS inverter to get wave exactly 180 out of phase. The CMOS does not contain any resistors, which makes it more power efficient than a regular resistor-MOSFET inverter.

## 1 Circuit Details

The phase180inverse circuit in eSIM had primarily two circuit design : (a) single stage n-MOSFET inverting amplifier and (b) CMOS inverter (a) MOSFET inverting amplifier A single stage NMOS amplifier was constructed using n-MOSFET in enhancement mode. The threshold voltage,  $V_{TH}$  of the MOSFET is 2.5 volts, and the DC supply voltage, is +15 volts. This simple enhancement-mode common source n-MOSFET amplifier configuration used a single 15 volt DC supply at the drain with load resistor  $R_D=500$  Ohms and generated the required gate voltage,  $V_G$  using a resistor divider. Voltage divider network with Resistors  $R_1$  and  $R_2$  was built to set gate voltage, where  $R_1$  and  $R_2$  were set as  $R_1 = 200k\Omega$  and  $R_2 = 100k\Omega$ . (xM1 Phase180 Net\_C1-Pad1\_ Phase180 Phase180 sky130\_fd\_pr\_nfet\_01v8 w=.42 l=.5 ) The inverted and amplified output of the nMOS inverter serves as input to CMOS inverter (b) CMOS inverter: A CMOS inverter was constructed in eSIM from a PMOS and a NMOS FETs connected at the drain and gate terminals. The input is connected to the gate terminal of both the transistors such that both can be driven directly with input voltages.  $V_{OUT}$  is connected to the drain terminals. The output of the single stage MOSFET amplifier serves as gate voltage to both MOSFETS.

(xM3 Net\_M3-Pad1\_ Phase180 OUT Net\_M3-Pad1\_ sky130\_fd\_pr\_pfet\_01v8 w=1 l=0.5 xM2 OUT Phase180 GND GND sky130\_fd\_pr\_nfet\_01v8 w=.42 l=.5)

## 2 Implemented Circuit

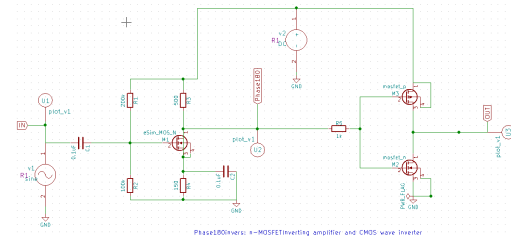


Figure 1: Implemented circuit diagram.

## 3 Implemented Waveforms

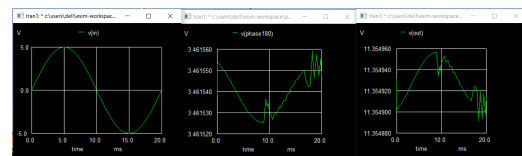


Figure 2: Implemented waveform.

## References

- [1] E. S. K. Er Kunal Ghosh. <https://www.udemy.com/course/vsd-intern-10-bit-dac-design-using-esim-and-sky130/learn/lecture/27028946#overview>. <https://www.udemy.com/course/vlsi-academy-circuit-design/>.
- [2] <https://www.udemy.com/course/vsd-intern-10-bit-dac-design-using-esim-and-sky130/learn/lecture/27028946#overview>. Mosfet amplifier. <https://www.electronicstutorials.ws/amplifier/mosfet-amplifier.html>.